

Day : Saturday
 Date: 3/17/2007

Time: 07:12:59

PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = DWILINSKI

First Name = ROBERT

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10479856	7081162	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	DWILINSKI, ROBERT
10479857	Not Issued	71	06/09/2004	METHOD OF FORMING GALLIUM-CONTAINING NITRIDE BULK SINGLE CRYSTAL ON HETEROGENEOUS SUBSTRATE	DWILINSKI, ROBERT
10479858	Not Issued	71	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	DWILINSKI, ROBERT
10493594	Not Issued	61	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	DWILINSKI, ROBERT
10493746	7057211	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	DWILINSKI, ROBERT
10493747	7132730	150	04/26/2004	BULK NITRIDE MONOCRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	DWILINSKI, ROBERT
10514429	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	DWILINSKI, ROBERT
10514638	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	DWILINSKI, ROBERT
10514639	Not Issued	30	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	DWILINSKI, ROBERT

<u>10519141</u>	Not Issued	71	12/27/2004	Process for obtaining of bulk monocrystalline gallium-containing nitride	DWILINSKI, ROBERT
<u>10519501</u>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	DWILINSKI, ROBERT
<u>10537804</u>	Not Issued	25	06/07/2005	Process for obtaining bulk monocrystalline gallium-containing nitride	DWILINSKI, ROBERT
<u>10538349</u>	Not Issued <i>Applicants'</i> <i>Invention</i>	30	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-containing nitride	DWILINSKI, ROBERT
<u>10538407</u>	Not Issued	30	06/10/2005	Substrate for epitaxy and method of preparing the same	DWILINSKI, ROBERT
<u>10538654</u>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	DWILINSKI, ROBERT
<u>11589058</u>	Not Issued	25	10/30/2006	Bulk nitride mono-crystal including substrate for epitaxy	DWILINSKI, ROBERT
<u>11629109</u>	Not Issued	19	01/01/0001	Bulk mono-crystalline gallium-containing nitride and its application	DWILINSKI, ROBERT
<u>11629125</u>	Not Issued	19	01/01/0001	High electron mobility transistor (hemt) made of layers of group xiii element nitrides and manufacturing method thereof	DWILINSKI, ROBERT
<u>10147318</u>	6656615	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	DWILINSKI, ROBERT TOMASZ
<u>10147319</u>	7160388	150	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	DWILINSKI, ROBERT TOMASZ
<u>10682891</u>	Not Issued	41	10/14/2003	Bulk monocrystalline gallium nitride	DWILINSKI, ROBERT TOMASZ

Inventor Search Completed: No Records to Display.

Search Another: Inventor

Last Name

Dwilinski

First Name

Robert

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PALM INTRANET

Day : Saturday
Date: 3/17/2007

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Inventor Name Search Result

Your Search was:

Last Name = DORADZINSKI

First Name = ROMAN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10479856	7081162	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	DORADZINSKI, ROMAN
10479857	Not Issued	71	06/09/2004	METHOD OF FORMING GALLIUM-CONTAINING NITRIDE BULK SINGLE CRYSTAL ON HETEROGENEOUS SUBSTRATE	DORADZINSKI, ROMAN
10479858	Not Issued	71	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	DORADZINSKI, ROMAN
10493594	Not Issued	61	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	DORADZINSKI, ROMAN
10493746	7057211	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	DORADZINSKI, ROMAN
10493747	7132730	150	04/26/2004	BULK NITRIDE MONOCRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	DORADZINSKI, ROMAN
10514429	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	DORADZINSKI, ROMAN
10514638	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	DORADZINSKI, ROMAN
10514639	Not Issued	30	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	DORADZINSKI, ROMAN

<u>10519141</u>	Not Issued	71	12/27/2004	Process for obtaining of bulk monocrystalline gallium-containing nitride	DORADZINSKI, ROMAN
<u>10519501</u>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	DORADZINSKI, ROMAN
<u>10537804</u>	Not Issued	25	06/07/2005	Process for obtaining bulk monocrystalline gallium-containing nitride	DORADZINSKI, ROMAN
<u>10538349</u>	Not Issued	30	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-containing nitride	DORADZINSKI, ROMAN
<u>10538407</u>	Not Issued	30	06/10/2005	Substrate for epitaxy and method of preparing the same	DORADZINSKI, ROMAN
<u>10538654</u>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	DORADZINSKI, ROMAN
<u>11589058</u>	Not Issued	25	10/30/2006	Bulk nitride mono-crystal including substrate for epitaxy	DORADZINSKI, ROMAN
<u>10147318</u>	6656615	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	DORADZINSKI, ROMAN MAREK
<u>10147319</u>	7160388	150	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	DORADZINSKI, ROMAN MAREK
<u>10479807</u>	Not Issued	100	12/05/2003	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	DORADZINSKI, ROMAN MAREK
<u>10682891</u>	Not Issued	41	10/14/2003	Bulk monocrystalline gallium nitride	DORADZINSKI, ROMAN MAREK

Inventor Search Completed: No Records to Display.

Search Another: Inventor	Last Name	First Name
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Day : Saturday
 Date: 3/17/2007

Time: 07:13:47

PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = GARCZYNSKI

First Name = JERZY

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10147318	6656615	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	GARCZYNSKI, JERZY
10147319	7160388	150	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	GARCZYNSKI, JERZY
10479807	Not Issued	100	12/05/2003	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	GARCZYNSKI, JERZY
10479856	7081162	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	GARCZYNSKI, JERZY
10479857	Not Issued	71	06/09/2004	METHOD OF FORMING GALLIUM-CONTAINING NITRIDE BULK SINGLE CRYSTAL ON HETEROGENEOUS SUBSTRATE	GARCZYNSKI, JERZY
10479858	Not Issued	71	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	GARCZYNSKI, JERZY
10493594	Not Issued	61	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	GARCZYNSKI, JERZY
10493746	7057211	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	GARCZYNSKI, JERZY
10493747	7132730	150	04/26/2004	BULK NITRIDE MONO-	GARCZYNSKI,

				CRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	JERZY
<u>10514429</u>	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	GARCZYNSKI, JERZY
<u>10514638</u>	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	GARCZYNSKI, JERZY
<u>10514639</u>	Not Issued	30	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	GARCZYNSKI, JERZY
<u>10519141</u>	Not Issued	71	12/27/2004	Process for obtaining of bulk monocrystalline gallium-containing nitride	GARCZYNSKI, JERZY
<u>10519501</u>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	GARCZYNSKI, JERZY
<u>10537804</u>	Not Issued	25	06/07/2005	Process for obtaining bulk monocrystalline gallium-containing nitride	GARCZYNSKI, JERZY
<u>10538349</u>	Not Issued	30	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-containing nitride	GARCZYNSKI, JERZY
<u>10538407</u>	Not Issued	30	06/10/2005	Substrate for epitaxy and method of preparing the same	GARCZYNSKI, JERZY
<u>10538654</u>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	GARCZYNSKI, JERZY
<u>10682891</u>	Not Issued	41	10/14/2003	Bulk monocrystalline gallium nitride	GARCZYNSKI, JERZY
<u>11589058</u>	Not Issued	25	10/30/2006	Bulk nitride mono-crystal including substrate for epitaxy	GARCZYNSKI, JERZY

Inventor Search Completed: No Records to Display.

Search Another: Inventor

Last Name	First Name
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Day : Saturday
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Time: 07:14:21

PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = SIERZPUTOWSKI

First Name = LESZEK

Application#	Patent#	Status	Date Filed	Title	Inventor Name
10479856	7081162	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	SIERZPUTOWSKI, LESZEK
10479857	Not Issued	71	06/09/2004	METHOD OF FORMING GALLIUM-CONTAINING NITRIDE BULK SINGLE CRYSTAL ON HETEROGENEOUS SUBSTRATE	SIERZPUTOWSKI, LESZEK
10479858	Not Issued	71	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	SIERZPUTOWSKI, LESZEK
10493594	Not Issued	61	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	SIERZPUTOWSKI, LESZEK
10493746	7057211	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	SIERZPUTOWSKI, LESZEK
10514429	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	SIERZPUTOWSKI, LESZEK
10514638	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	SIERZPUTOWSKI, LESZEK
10537804	Not Issued	25	06/07/2005	Process for obtaining bulk mono-crystalline gallium-containing nitride	SIERZPUTOWSKI, LESZEK
10538349	Not Issued	30	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-	SIERZPUTOWSKI, LESZEK

				containing nitride	
<u>10538407</u>	Not Issued	30	06/10/2005	Substrate for epitaxy and method of preparing the same	SIERZPUTOWSKI, LESZEK
<u>10538654</u>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	SIERZPUTOWSKI, LESZEK
<u>10514639</u>	Not Issued	30	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	SIERZPUTOWSKI, LESZEK P
<u>10493747</u>	7132730	150	04/26/2004	BULK NITRIDE MONOCRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	SIERZPUTOWSKI, LESZEK P.
<u>10519501</u>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	SIERZPUTOWSKI, LESZEK P.
<u>11589058</u>	Not Issued	25	10/30/2006	Bulk nitride mono-crystal including substrate for epitaxy	SIERZPUTOWSKI, LESZEK P.
<u>10147318</u>	6656615	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	SIERZPUTOWSKI, LESZEK PIOTR
<u>10147319</u>	7160388	150	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	SIERZPUTOWSKI, LESZEK PIOTR
<u>10479807</u>	Not Issued	100	12/05/2003	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	SIERZPUTOWSKI, LESZEK PIOTR
<u>10682891</u>	Not Issued	41	10/14/2003	Bulk monocrystalline gallium nitride	SIERZPUTOWSKI, LESZEK PIOTR

Inventor Search Completed: No Records to Display.

Search Another: Inventor

Last Name	First Name
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PALM INTRANET

Day : Saturday
 Date: 3/17/2007
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Inventor Name Search Result

Your Search was:

Last Name = KANBARA

First Name = YASUO

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>10147318</u>	6656615	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	KANBARA, YASUO
<u>10147319</u>	7160388	150	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	KANBARA, YASUO
<u>10192246</u>	7042830	150	07/09/2002	PHASE-CHANGE OPTICAL INFORMATION RECORDING MEDIUM, AND OPTICAL INFORMATION RECORDING AND REPRODUCING APPARATUS AND METHOD FOR THE SAME	KANBARA, YASUO
<u>10479807</u>	Not Issued	100	12/05/2003	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	KANBARA, YASUO
<u>10479856</u>	7081162	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	KANBARA, YASUO
<u>10479857</u>	Not Issued	71	06/09/2004	METHOD OF FORMING GALLIUM-CONTAINING NITRIDE BULK SINGLE CRYSTAL ON HETEROGENEOUS SUBSTRATE	KANBARA, YASUO
<u>10479858</u>	Not Issued	71	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	KANBARA, YASUO
<u>10493594</u>	Not	61	04/26/2004	Light emitting element structure	KANBARA,

	Issued			using nitride bulk single crystal layer	YASUO
<u>10493746</u>	<u>7057211</u>	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	KANBARA, YASUO
<u>10493747</u>	<u>7132730</u>	150	04/26/2004	BULK NITRIDE MONOCRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	KANBARA, YASUO
<u>10514429</u>	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	KANBARA, YASUO
<u>10514638</u>	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	KANBARA, YASUO
<u>10514639</u>	Not Issued	30	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	KANBARA, YASUO
<u>10519141</u>	Not Issued	71	12/27/2004	Process for obtaining of bulk monocrystalline gallium-containing nitride	KANBARA, YASUO
<u>10519501</u>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	KANBARA, YASUO
<u>10537804</u>	Not Issued	25	06/07/2005	Process for obtaining bulk monocrystalline gallium-containing nitride	KANBARA, YASUO
<u>10538349</u>	Not Issued	30	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-containing nitride	KANBARA, YASUO
<u>10538407</u>	Not Issued	30	06/10/2005	Substrate for epitaxy and method of preparing the same	KANBARA, YASUO
<u>10538654</u>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	KANBARA, YASUO
<u>10682891</u>	Not Issued	41	10/14/2003	Bulk monocrystalline gallium nitride	KANBARA, YASUO
<u>11589058</u>	Not Issued	25	10/30/2006	Bulk nitride mono-crystal including substrate for epitaxy	KANBARA, YASUO

Inventor Search Completed: No Records to Display.

Search Another: Inventor

Last Name

Kanbara

First Name

Yasuo

Search